

Specification of Photodiode

PD006

[PIN-PD]

1) Commodity Type and Physical Characteristics.

1. Structure : Planer type PIN Photodiode
2. Electrode Top Side Anode side : Aluminum Alloy
Bottom Side Cathode side: Au Alloy
3. Electrode Pad ϕ 130um Fig.1
4. Chip Size : 0.6mmx0.6mm Fig.1
5. Active Area : 0.44mmx0.44mm Fig.1
6. Chip Thickness : 0.20±0.05mm Fig.2

2) Electro-Optical Characteristics (Ta=25°C)

Item	Symbol	Condition	Minimum	Typical	Maximum	unit
Reverse Photo Current	I_L	$V_R=10V, L=1000Lx$		2		uA
Reverse Dark Current	I_D	$V_R=10V$			10	nA
Reverse Breakdown Voltage	$V_{(BR)R}$	$I_R=100uA, L=0Lx$		170		V
Open Circuit Voltage	V_{OC}	$V_R=10V, L=1000Lx$		390		mV
Spectral Responsivity (Peak)	I_P			900		nm
Total Capacitance	C_T	$V_R=10V, f=1MHz$		6		pF
Rise/Fall Time(10% ~ 90%)	t_r	$R_L=1KW, V_R=10V$		6		ns
	t_f			6		ns

[Unit : um]

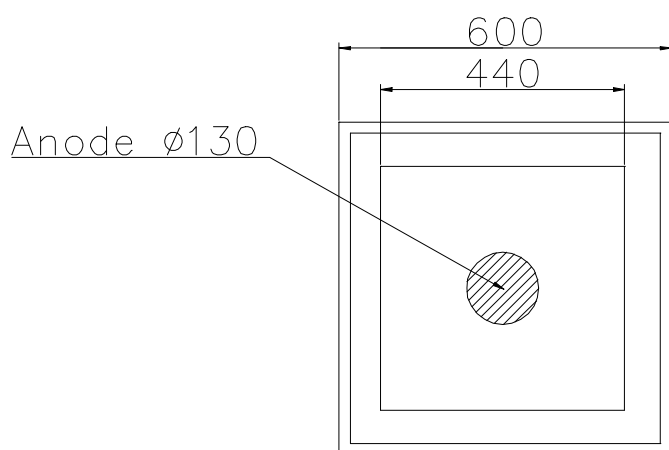


Fig.1 Electrode Pattern and active area

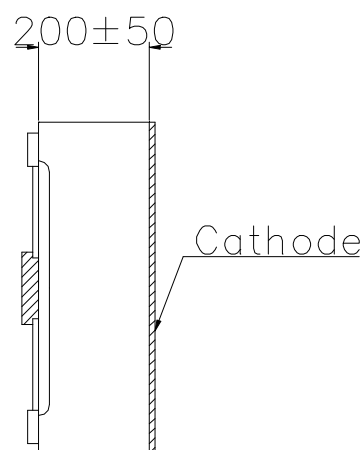


Fig.2 Chip cross section